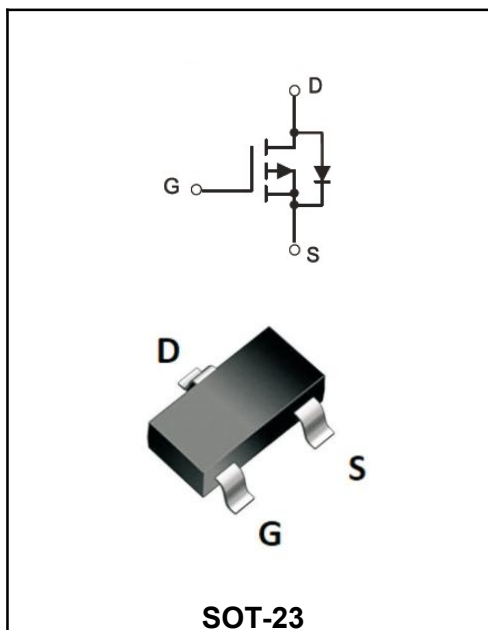


-40V P-Channel Plastic-Encapsulate MOSFET

MAIN CHARACTERISTICS

I_D	-3A
V_{DSS}	-40V
R_{DS(on)}-typ(@V_{GS}-10V)	<138mΩ(Typ:110mΩ)
R_{DS(on)}-typ(@V_{GS}-4.5V)	<175mΩ(Typ:140mΩ)



FEATURES

- ◆Trench FET Power MOSFET
- ◆Surface Mount device
- ◆DC/DC Converter

Mechanical Data

- ◆SOT-23 Small Outline Plastic Package
- ◆Epoxy UL: 94V-0
- ◆Mounting Position: Any

Marking Code	
YFW3P04A	3P04A

Absolute Maximum Ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current TA=25℃ TA=100℃	I_D	-3 -1.9	A
Pulsed Drain Current(Note1)	I_{DM}	-20	A
Total Power Dissipation(Note2) TA=25℃ TA=100℃	P_D	1 0.4	W
Junction Temperature	T_J	-55-+150	℃
Storage Temperature	T_{stg}	-55-+150	℃
Thermal Resistance From Junction to Ambient (Note3)	R_{θJA}	125	℃/W

Electrical Characteristics (Ta=25℃,unless otherwise noted)

arameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-40			V
Gate-Threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.8	-2.5	V
Gate-body Leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$			-1	uA
		$V_{DS}=-40V, V_{GS}=0V, T_J=150^\circ C$			-100	
Drain-Source On-Resistance(Note1)	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-2A$		140	175	mΩ
		$V_{GS}=-10V, I_D=-3A$		110	138	
Body diode voltage	V_{SD}	$I_S=-3A, V_{GS}=0$		-0.85	-1.2	V
Gate resistance	R_G	$f=1MHz$		20		Ω
Maximum Body-Diode Continuous Current	I_S				-3	A
Input capacitance	C_{iss}	$V_{DS}=-20V$ $V_{GS}=0V$ $f=1MHz$		400		pF
Output capacitance	C_{oss}			50		
Reverse Transfer capacitance	C_{rss}			40		
Total gate charge	Q_g	$V_{DS}=-20V$ $V_{GS}=-10V$ $I_D=-3A$		8.5		nC
Gate-source charge	Q_{gs}			1		
Gate-drain charge	Q_{gd}			2		
Reverse Recovery Charge	Q_{rr}	$I_F=-3A$ $di/dt=100A/\mu s$		31		nC
Reverse Recovery Time	t_{rr}			34		ns
Turn-on Time	$t_{d(on)}$	$V_{GS}=-10V$ $V_{DD}=-20V$ $I_D=3A$ $R_{GEN}=3\Omega$		6		ns
Rise time	t_r			6		
Turn-off Time	$t_{d(off)}$			31		
Fall time	$t_{d(on)}$			19		

Notes:

1.Repetitive rating; pulse width limited by max. junction temperature.

2.Pd is based on max. junction temperature, using junction-case thermal resistance.

3.The value of $R_{\theta JA}$ is measured with the device mounted on the minimum recommend pad size, in the still air environment with $T_A=25^\circ C$. The maximum allowed junction temperature of $150^\circ C$. The value in any given application depends on the user's specific board design.

Typical Characteristics

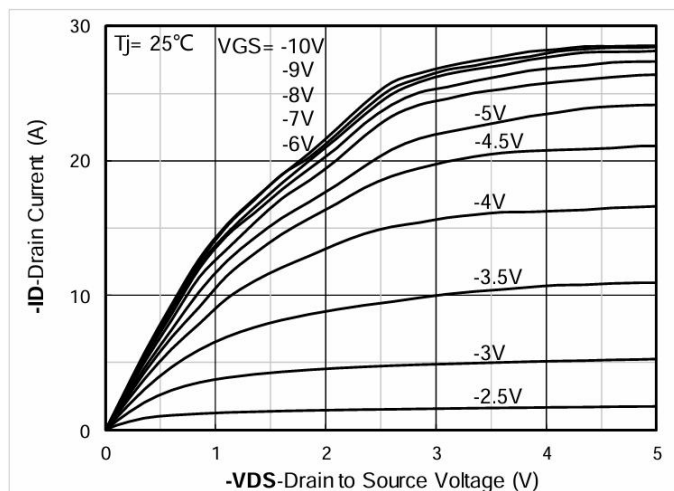


Figure 1. Output Characteristics

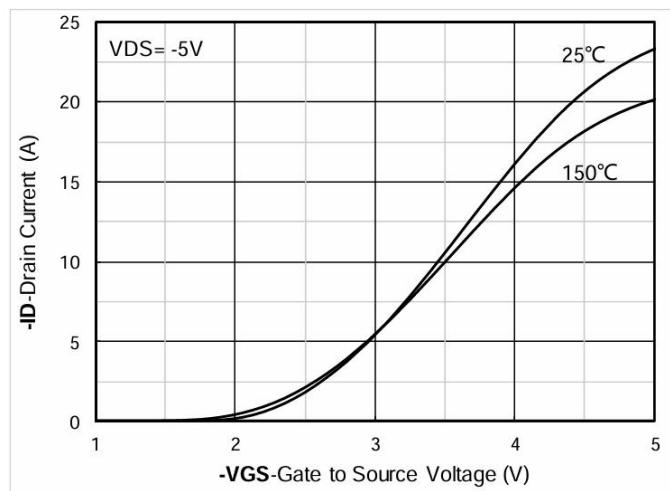


Figure 2. Transfer Characteristics

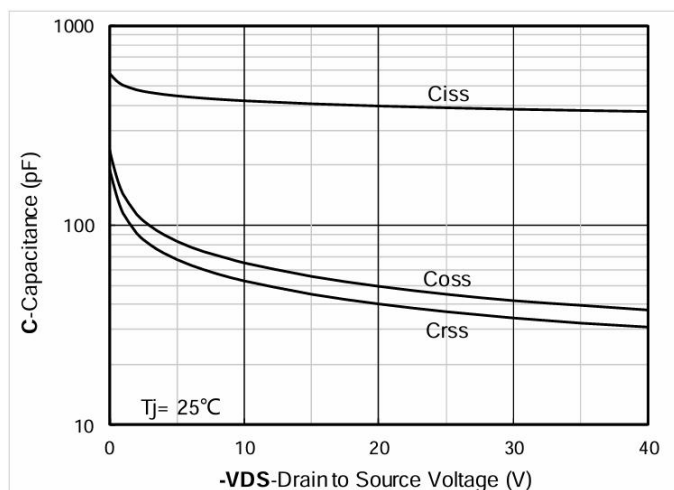


Figure 3. Capacitance Characteristics

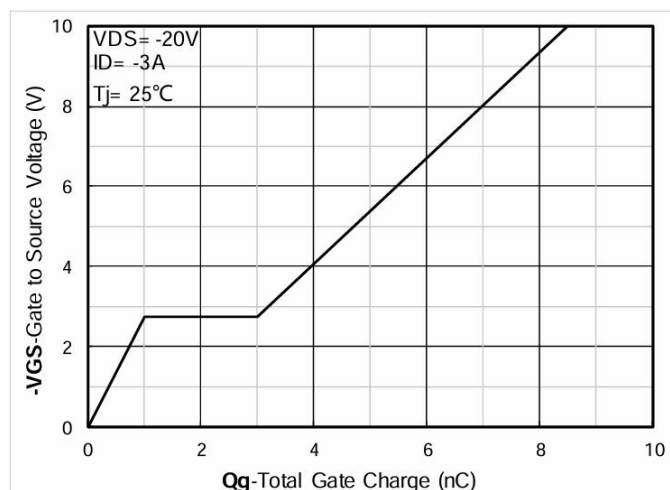


Figure 4. Gate Charge

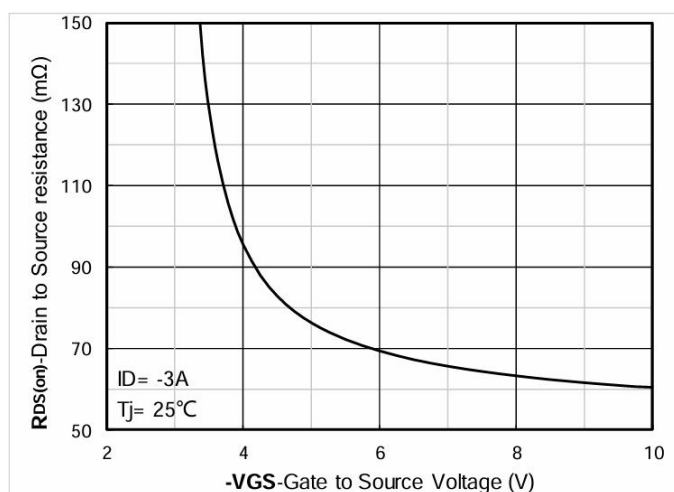


Figure 5. On-Resistance vs Gate to Source Voltage

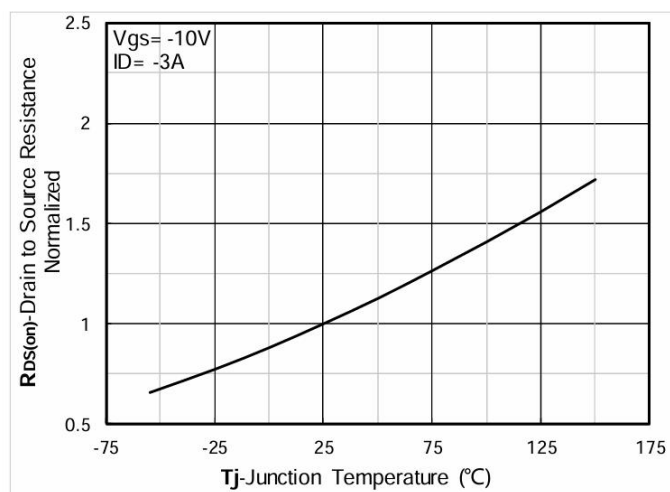


Figure 6. Normalized On-Resistance

Typical Characteristics

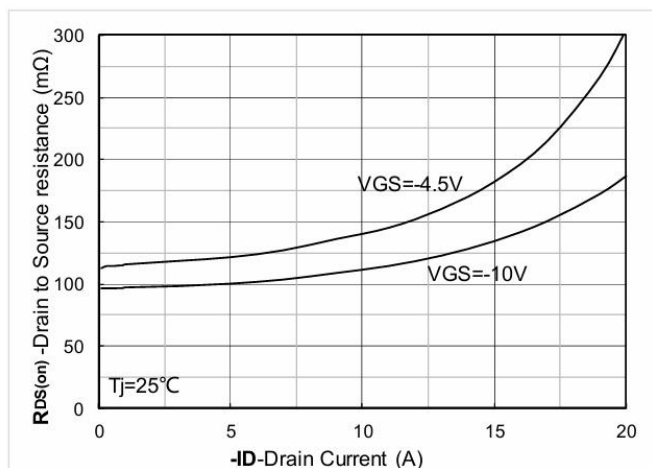


Figure 7. $R_{DS(on)}$ VS Drain Current; typical values

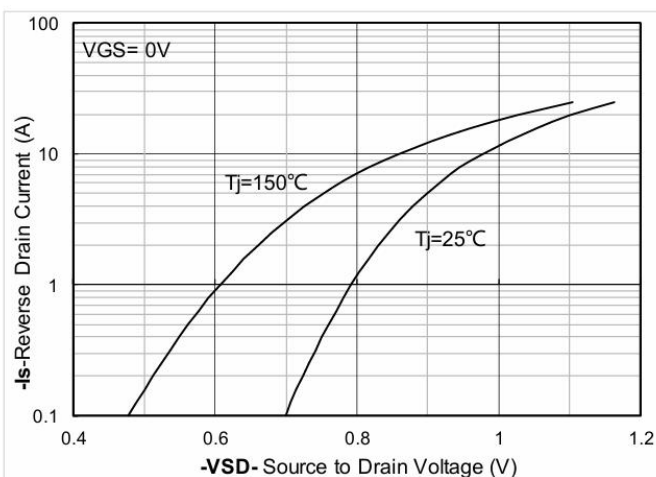


Figure 8. Forward characteristics of reverse diode; typical values

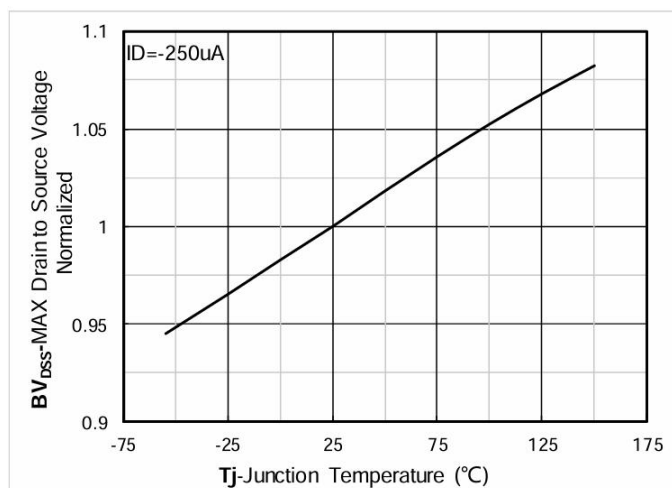


Figure 9. Normalized breakdown voltage

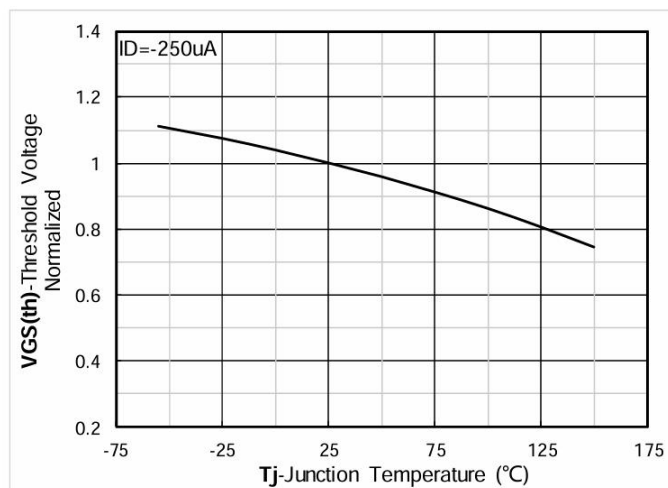


Figure 10. Normalized Threshold voltage

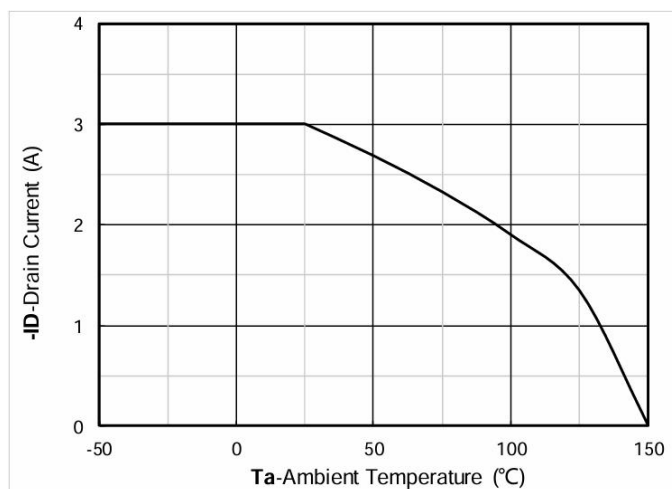


Figure 11. Current dissipation

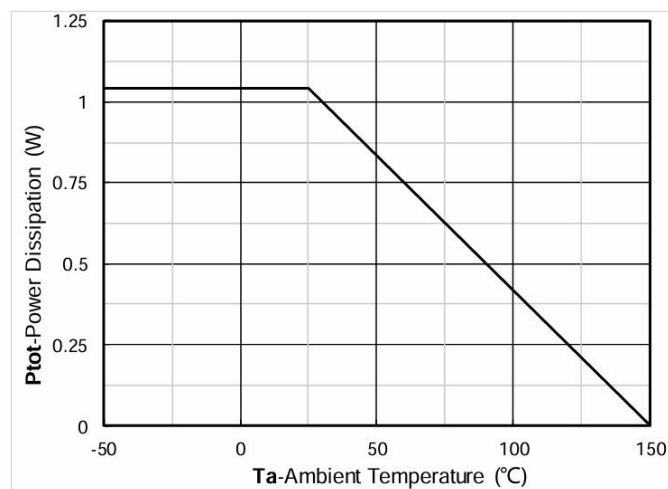


Figure 12. Power dissipation

Ordering information

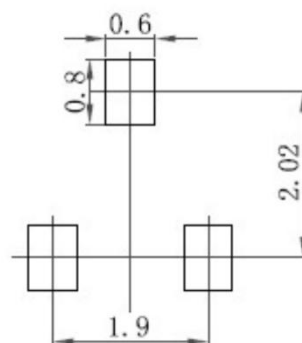
Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel, 7" reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-23

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
e	1.9		75	
e1	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

The recommended mounting pad size



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